

HSL226

Silicon Schottky Barrier Diode for High Speed Switching

REJ03G0016-0100Z

Rev.1.00

Apr.15.2003

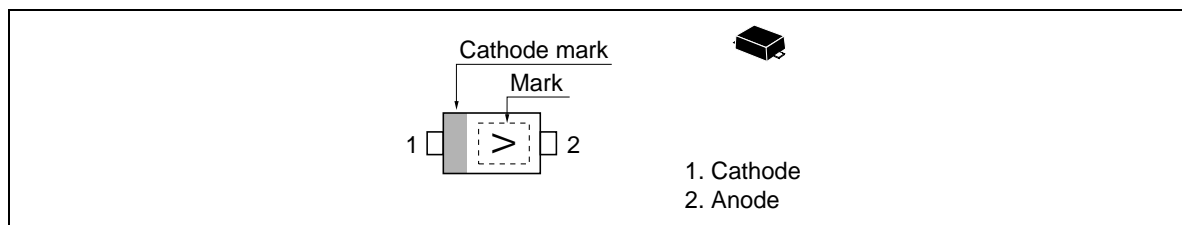
Features

- Low reverse current, Low capacitance.
- Extremely small Flat Package (EFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSL226	V	EFP

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	25	V
Non-Repetitive Peak forward surge current	I_{FSM}^{*1}	200	mA
Forward current	I_F	50	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: 1. 10 ms Sine Wave 1 pulse

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	0.33	V	$I_F = 1 \text{ mA}$
	V_{F2}	—	—	0.38	V	$I_F = 5 \text{ mA}$
Reverse current	I_R	—	—	0.45	μA	$V_R = 20 \text{ V}$
Capacitance	C	—	—	2.80	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$

Notes: 1. Please do not use the soldering iron due to avoid high stress to the EFP package.
 2. The material of lead is exposed for cutting plane. Therefore, soldering nature of lead tip part is considered as unquestioned. Please kindly consider soldering nature.

Main Characteristic

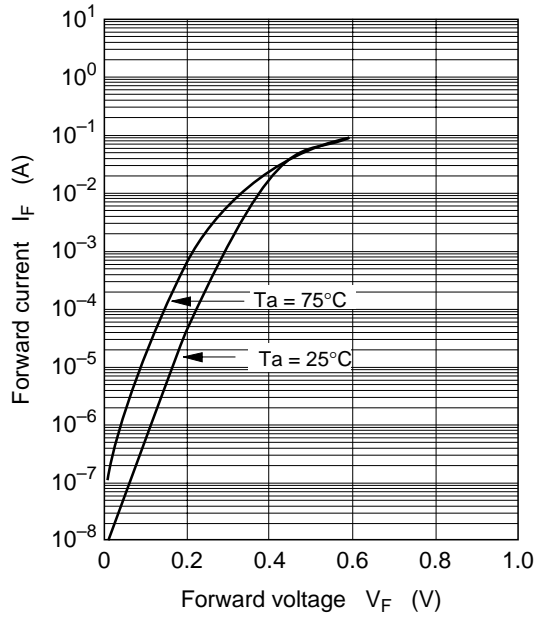


Fig.1 Forward current vs. Forward voltage

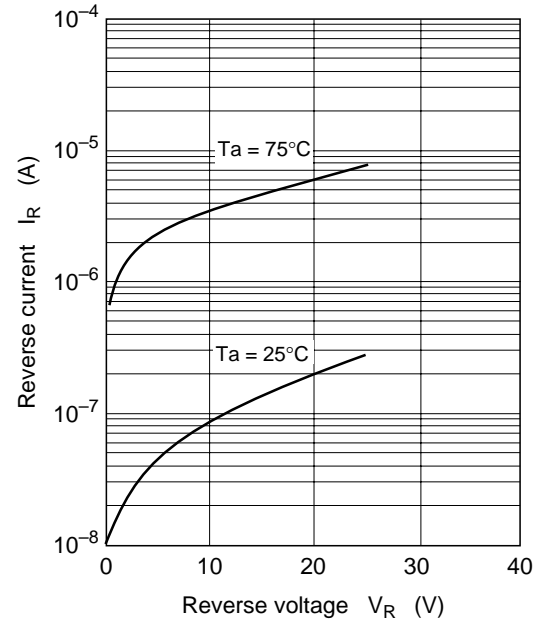


Fig.2 Reverse current vs. Reverse voltage

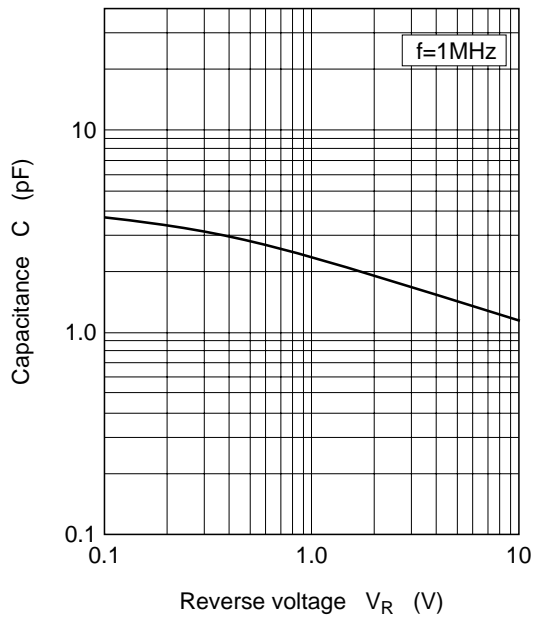
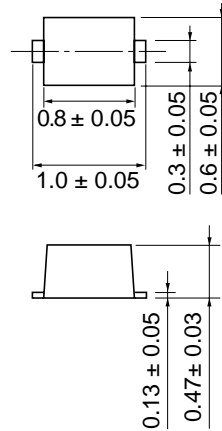


Fig.3 Capacitance vs. Reverse voltage

Package Dimensions

As of January, 2003

Unit: mm



Package Code	EFP
JEDEC	—
JEITA	—
Mass (reference value)	0.0007 g

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